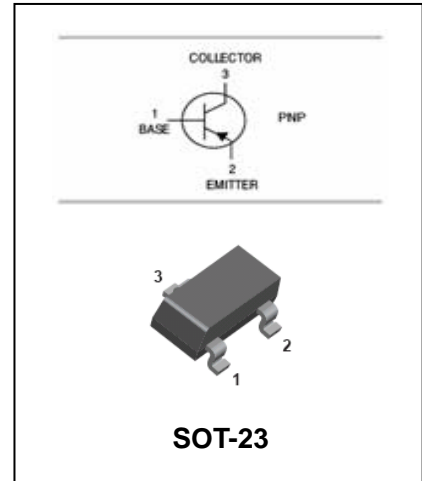


PNP general purpose Transistor

BC856/857/858

FEATURES

- Low current.(max.100mA).
- Low voltage..



APPLICATIONS

- General purpose switching and amplification.

ORDERING INFORMATION

Type No.	Marking	Package Code
BC856A/B	3A/3B	SOT-23
BC857A/B/C	3E/3F/3G	SOT-23
BC858A/B/C	3J/3K/3L	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	BC856	-80
		BC857	-50
		BC858	-30
V _{CEO}	Collector-Emitter Voltage	BC856	-65
		BC857	-45
		BC858	-30
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.1	A
P _C	Collector Dissipation	250	mW
T _j , T _{stg}	Junction and Storage Temperature	-65 to +150	°C



PNP general purpose Transistor

BC856/857/858

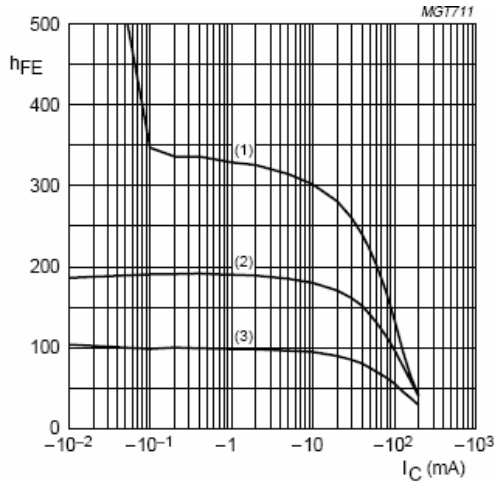
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage BC856 BC857 BC858	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-80 -50 -30			V
Collector-emitter breakdown voltage BC856 BC857 BC858	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-65 -45 -30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$		-1	-15	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain BC856A,857A,858A BC856B,857B,858B BC857C,858C	h_{FE}	$V_{CE}=-5V, I_C=-2mA$	125 220 420		250 475 800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-5mA$ $I_C=-10mA, I_B=-0.5mA$			-0.65 -0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10mA, I_B=-0.5mA$ $I_C=-100mA, I_B=-5mA$		-0.7 -0.85		V
Base-emitter voltage	$V_{BE(on)}$	$I_C=-2mA, V_{CE}=-5V$ $I_C=-10mA, V_{CE}=-5V$	-0.6	-0.65	-0.75 -0.82	V
collector capacitance	C_c	$V_{CB}=-10V, I_E=I_e=0$ $f=1MHz$		4.5		pF
Transition frequency	F	$I_C=-200\mu A, V_{CE}=-5V,$ $R_S=2k\Omega, f=1kHz,$ $B=200Hz$		2	10	dB
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$	100			MHz

PNP general purpose Transistor

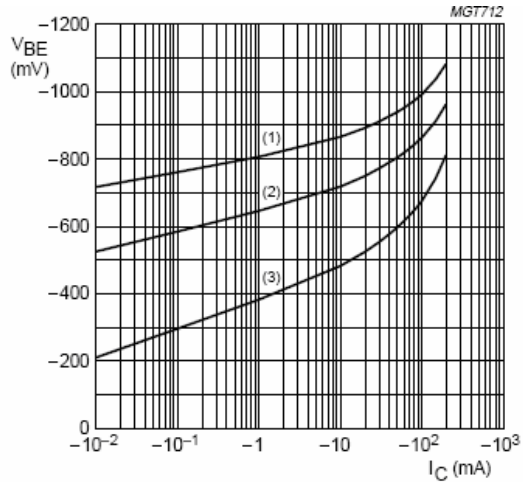
BC856/857/858

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



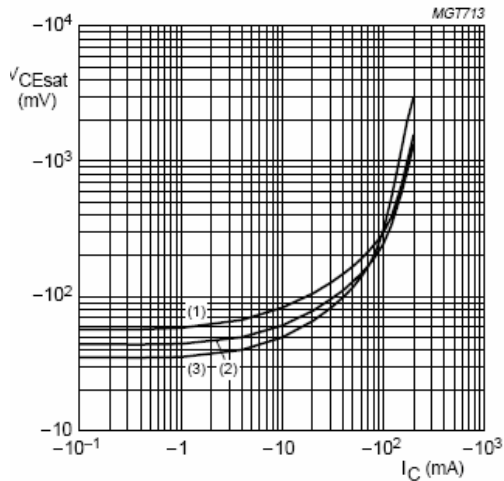
BC857A; $V_{CE} = -5\text{ V}$.
 (1) $T_{amb} = 150^\circ\text{C}$.
 (2) $T_{amb} = 25^\circ\text{C}$.
 (3) $T_{amb} = -55^\circ\text{C}$.

Fig.1 DC current gain as a function of collector current; typical values.



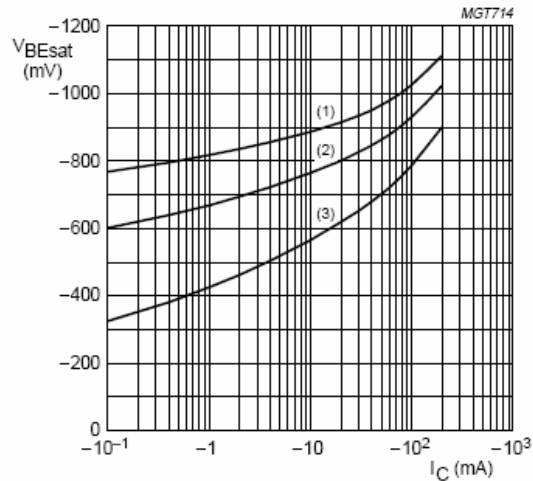
BC857A; $V_{CE} = -5\text{ V}$.
 (1) $T_{amb} = -55^\circ\text{C}$.
 (2) $T_{amb} = 25^\circ\text{C}$.
 (3) $T_{amb} = 150^\circ\text{C}$.

Fig.2 Base-emitter voltage as a function of collector current; typical values.



BC857A; $I_C/I_B = 20$.
 (1) $T_{amb} = 150^\circ\text{C}$.
 (2) $T_{amb} = 25^\circ\text{C}$.
 (3) $T_{amb} = -55^\circ\text{C}$.

Fig.3 Collector-emitter saturation voltage as a function of collector current; typical values.

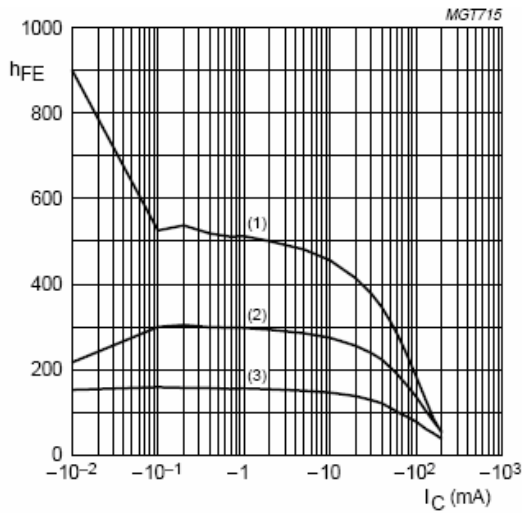


BC857A; $I_C/I_B = 20$.
 (1) $T_{amb} = -55^\circ\text{C}$.
 (2) $T_{amb} = 25^\circ\text{C}$.
 (3) $T_{amb} = 150^\circ\text{C}$.

Fig.4 Base-emitter saturation voltage as a function of collector current; typical values.

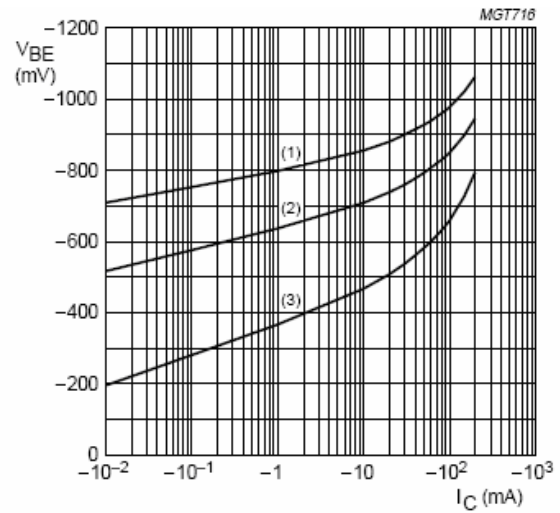
PNP general purpose Transistor

BC856/857/858



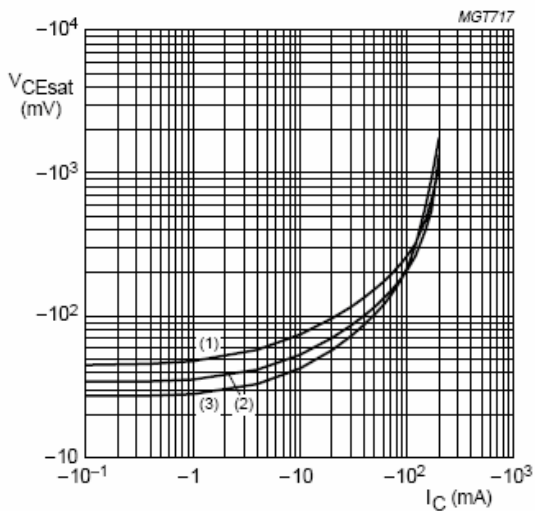
BC857B; $V_{CE} = -5\text{ V}$.
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

Fig.5 DC current gain as a function of collector current; typical values.



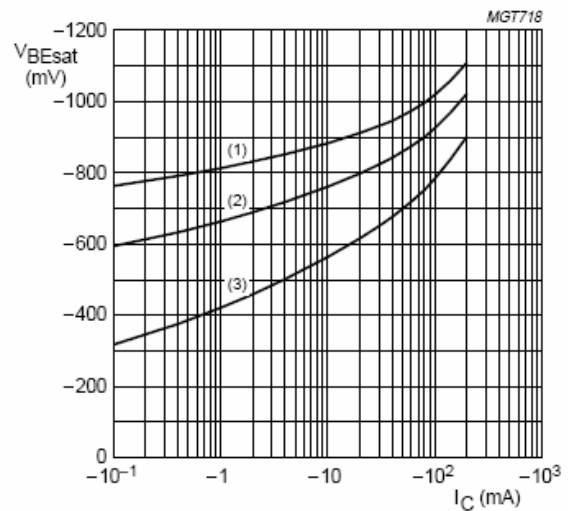
BC857B; $V_{CE} = -5\text{ V}$.
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$.

Fig.6 Base-emitter voltage as a function of collector current; typical values.



BC857B; $I_C/I_B = 20$.
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

Fig.7 Collector-emitter saturation voltage as a

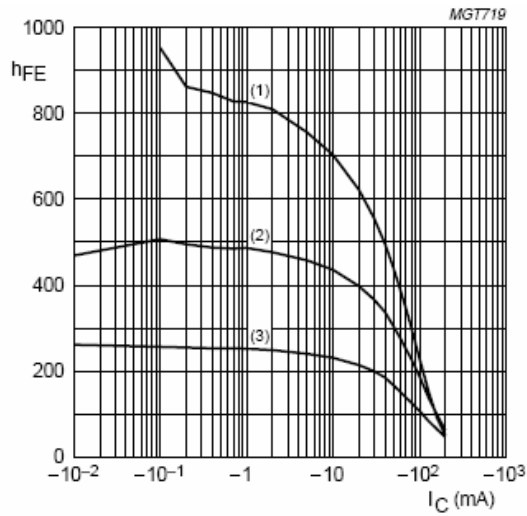


BC857B; $I_C/I_B = 20$.
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$.

Fig.8 Base-emitter saturation voltage as a

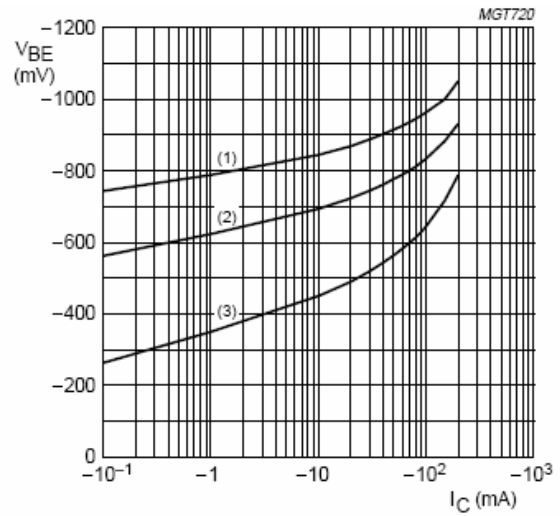
PNP general purpose Transistor

BC856/857/858



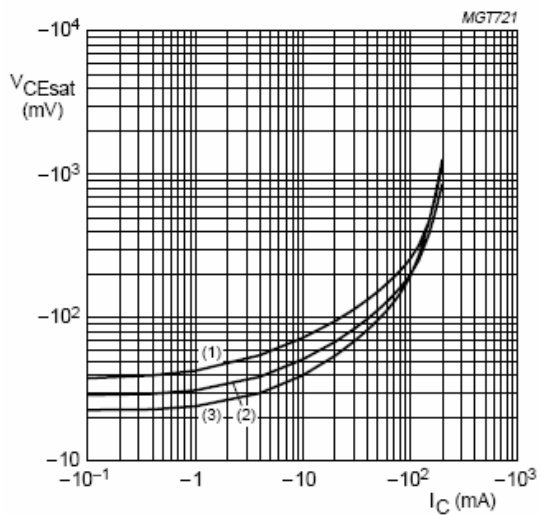
BC857C; $V_{CE} = -5\text{ V}$.
 (1) $T_{amb} = 150\text{ °C}$.
 (2) $T_{amb} = 25\text{ °C}$.
 (3) $T_{amb} = -55\text{ °C}$.

Fig.9 DC current gain as a function of collector current; typical values.



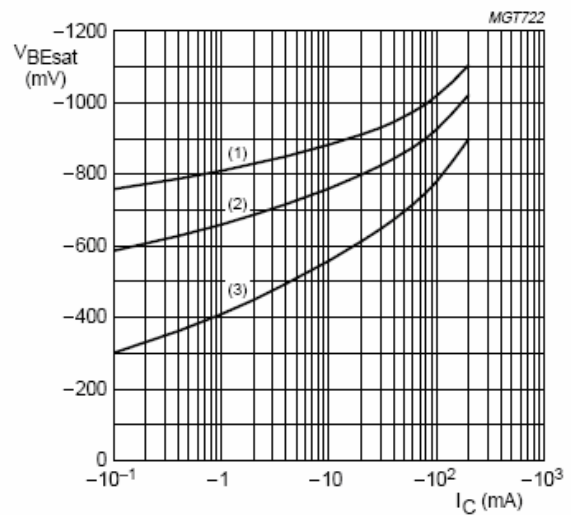
BC857C; $V_{CE} = -5\text{ V}$.
 (1) $T_{amb} = -55\text{ °C}$.
 (2) $T_{amb} = 25\text{ °C}$.
 (3) $T_{amb} = 150\text{ °C}$.

Fig.10 Base-emitter voltage as a function of collector current; typical values.



BC857C; $I_C/I_B = 20$.
 (1) $T_{amb} = 150\text{ °C}$.
 (2) $T_{amb} = 25\text{ °C}$.
 (3) $T_{amb} = -55\text{ °C}$.

Fig.11 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857C; $I_C/I_B = 20$.
 (1) $T_{amb} = -55\text{ °C}$.
 (2) $T_{amb} = 25\text{ °C}$.
 (3) $T_{amb} = 150\text{ °C}$.

Fig.12 Base-emitter saturation voltage as a function of collector current; typical values

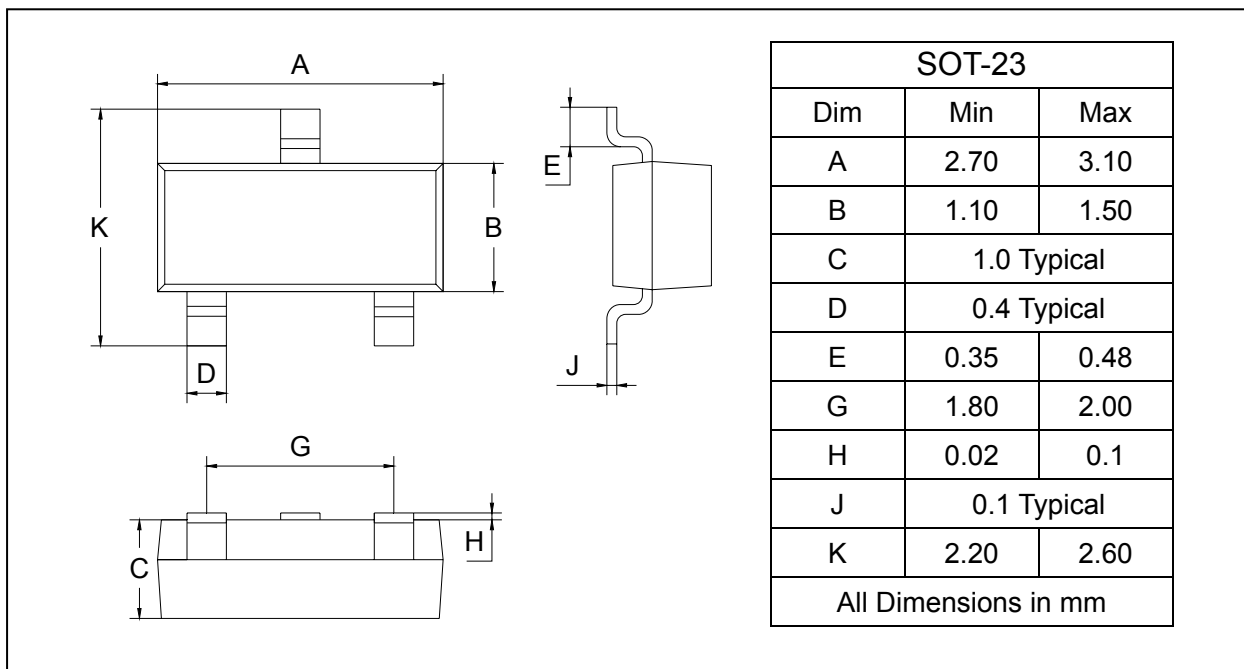
PNP general purpose Transistor

BC856/857/858

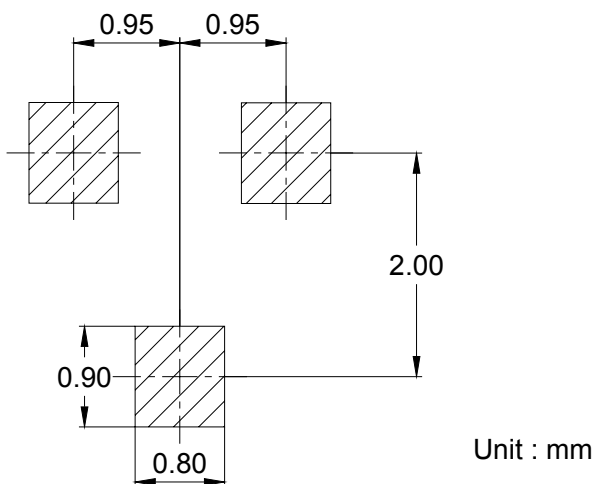
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BC856/857/858	SOT-23	3000/Tape&Reel